

CLAIMS

1. A method of driving an integrated circuit including a field-effect transistor, comprising
5 periodically applying positive and negative voltages, with reference to the voltage applied to the source and drain electrodes, to the gate electrode of the field-effect transistor.
2. The method according to claim 1, wherein the
10 field-effect transistor is a thin-film transistor.
3. The method according to claim 1, wherein the field-effect transistor comprises a semiconductor material containing an organic substance.
4. The method according to claim 1, wherein the
15 field-effect transistor comprises a semiconductor material containing amorphous silicon.
5. The method according to claim 1, wherein positive and negative voltage pulses, with reference to the voltage applied to the source and drain
20 electrodes, are applied alternately to the gate electrode of the field-effect transistor.
6. The method according to claim 1, wherein positive or negative voltage pulses, with reference to the voltage applied to the source and drain
25 electrodes, are continuously applied to the gate electrode of the field-effect transistor, and then one or more negative or positive voltage pulses

respectively are applied to the gate electrode.

7. The method according to claim 1, wherein the application of positive and negative voltage pulses is equivalently weighted by adjusting the duration or
5 pulse number of the positive and negative voltage pulses applied.

8. An integrated circuit to be driven by using the method according to claim 1.

9. An IC card to be driven by using the method
10 according to claim 1.

10. A light emitting diode device to be driven by using the method according to claim 1.

11. A liquid crystal device to be driven by using the method according to claim 1.